SZCJ

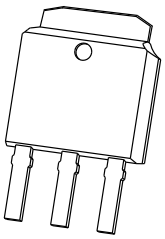
Shenzhen Changji Semiconductor Co., LTD.

TO-251S Plastic-Encapsulate MOSFETS

CJD04N65 N-Channel Power MOSFET

$V_{(BR)DSS}$	$R_{DS(on)}$TYP	I_D
650V	2.3Ω@10V	4A

TO-251S



1. GATE
2. DRAIN
3. SOURCE

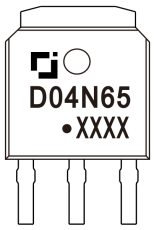
GENERAL DESCRIPTION

This advanced high voltage MOSFET is designed to stand high energy in the avalanche mode and switch efficiently. This new high energy device also offers a drain-to-source diode fast recovery time. Desighed for high voltage, high speed switching applications such as power supplies, converters, power motor controls and bridge circuits.

FEATURE

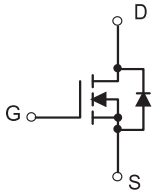
- High Current Rating
- Lower $R_{DS(on)}$
- Lower Capacitance
- Lower Total Gate Charge
- Tighter V_{SD} Specifications
- Avalanche Energy Specified

MARKING



D04N65 = Device code
Solid dot = Green molding compound device, if none, the normal device
XXXX=Code

EQUIVALENT CIRCUIT



Maximum ratings (T_a=25℃ unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	650	V
Gate-Source Voltage	V_{GS}	±30	
Continuous Drain Current	I_D	4.0	A
Pulsed Drain Current	I_{DM}	16	
Single Pulsed Avalanche Energy (note1)	E_{AS}	280	mJ
Power Dissipation	P_D	1.25	W
Thermal Resistance from Junction to Ambient	$R_{\theta JA}$	100	℃/W
Operating and Storage Temperature Range	T_J, T_{STG}	-55 ~+150	℃
Maximum lead temperure for soldering purposes , 1/8"from case for 5 seconds	T_L	260	

Electrical characteristics (T_a=25℃ unless otherwise noted)

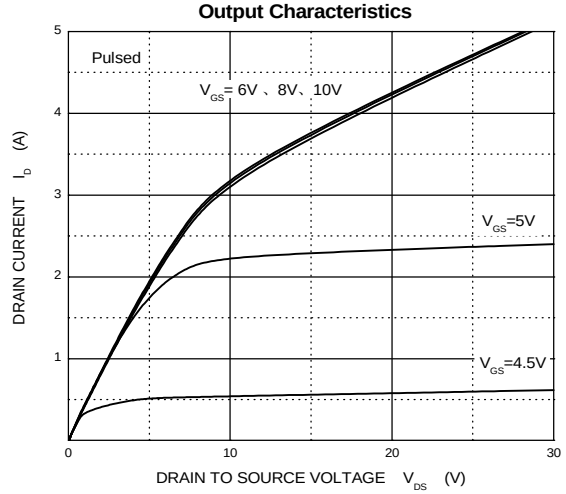
Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Off characteristics						
Drain-source breakdown voltage	$V_{(BR)DSS}$	V_{GS} = 0V, I_D =250μA	650			V
Drain-source diode forward voltage(note2)	V_{SD}	V_{GS} = 0V, I_S =4.0A			1.5	
Zero gate voltage drain current	I_{DSS}	V_{DS} =600V, V_{GS} =0V			25	μA
Gate-body leakage curren (note2)	I_{GSS}	V_{DS} =0V, V_{GS} =±30V			±100	nA
On characteristics (note2)						
Gate-threshold voltage	$V_{GS(th)}$	V_{DS} =V_{GS}, I_D =250μA	2.0	3.5	4.0	V
Static drain-source on-resistance	$R_{DS(on)}$	V_{GS} =10V, I_D =2.0A		2.3	3.0	Ω
Dynamic characteristics (note 3)						
Input capacitance	C_{iss}	V_{DS} =25V,V_{GS} =0V,f =1MHz			760	pF
Output capacitance	C_{oss}				180	
Reverse transfer capacitance	C_{rss}				20	
Switching characteristics (note 3)						
Total gate charge	Q_g	V_{DS} =480V,V_{GS} =10V,I_D =4.0A		5.0	10	nC
Gate-source charge	Q_{gs}			2.7		
Gate-drain charge	Q_{gd}			2.0		
Turn-on delay time (note3)	$t_{d(on)}$	V_{DD}=300V, V_{GS}=10V, R_G=9.1Ω, I_D =4.0A			20	ns
Turn-on rise time (note3)	t_r				10	
Turn-off delay time (note3)	$t_{d(off)}$				40	
Turn-off fall time (note3)	t_f				20	

Notes :

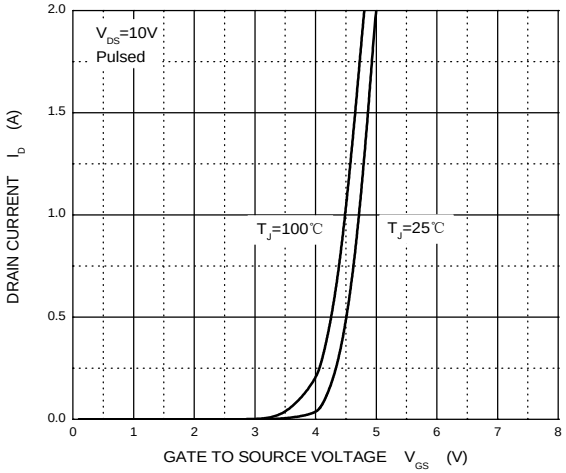
1. L=30mH, I_L=4 A, V_{DD}=100V, R_G=25Ω,Starting T_J=25℃.
2. Pulse Test : Pulse width≤300μs, duty cycle ≤2%.
3. These parameters have no way to verify.

Typical Characteristics

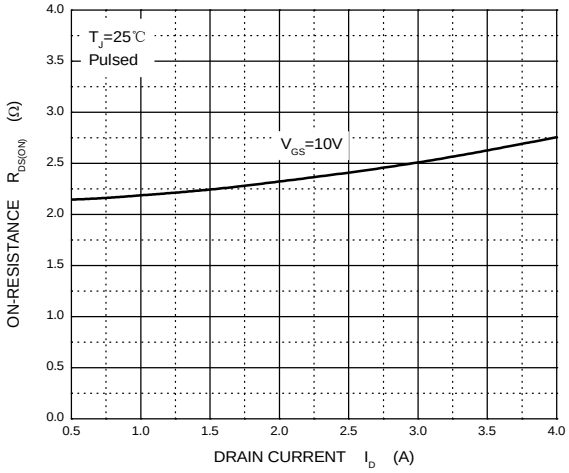
Output Characteristics



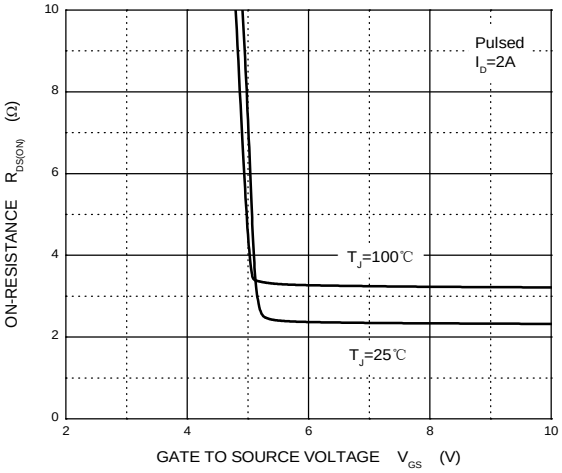
Transfer Characteristics



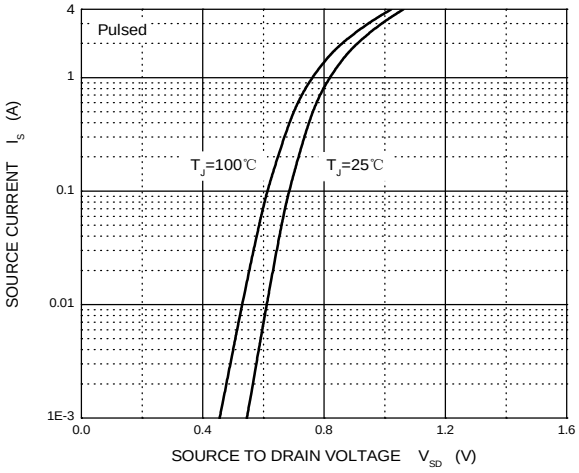
$R_{DS(ON)}$ —— I_D



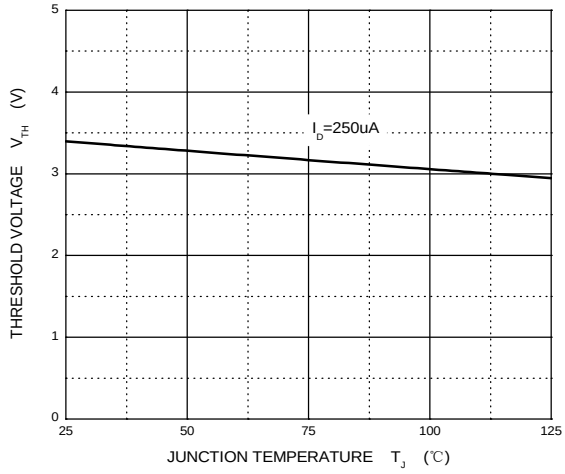
$R_{DS(ON)}$ —— V_{GS}



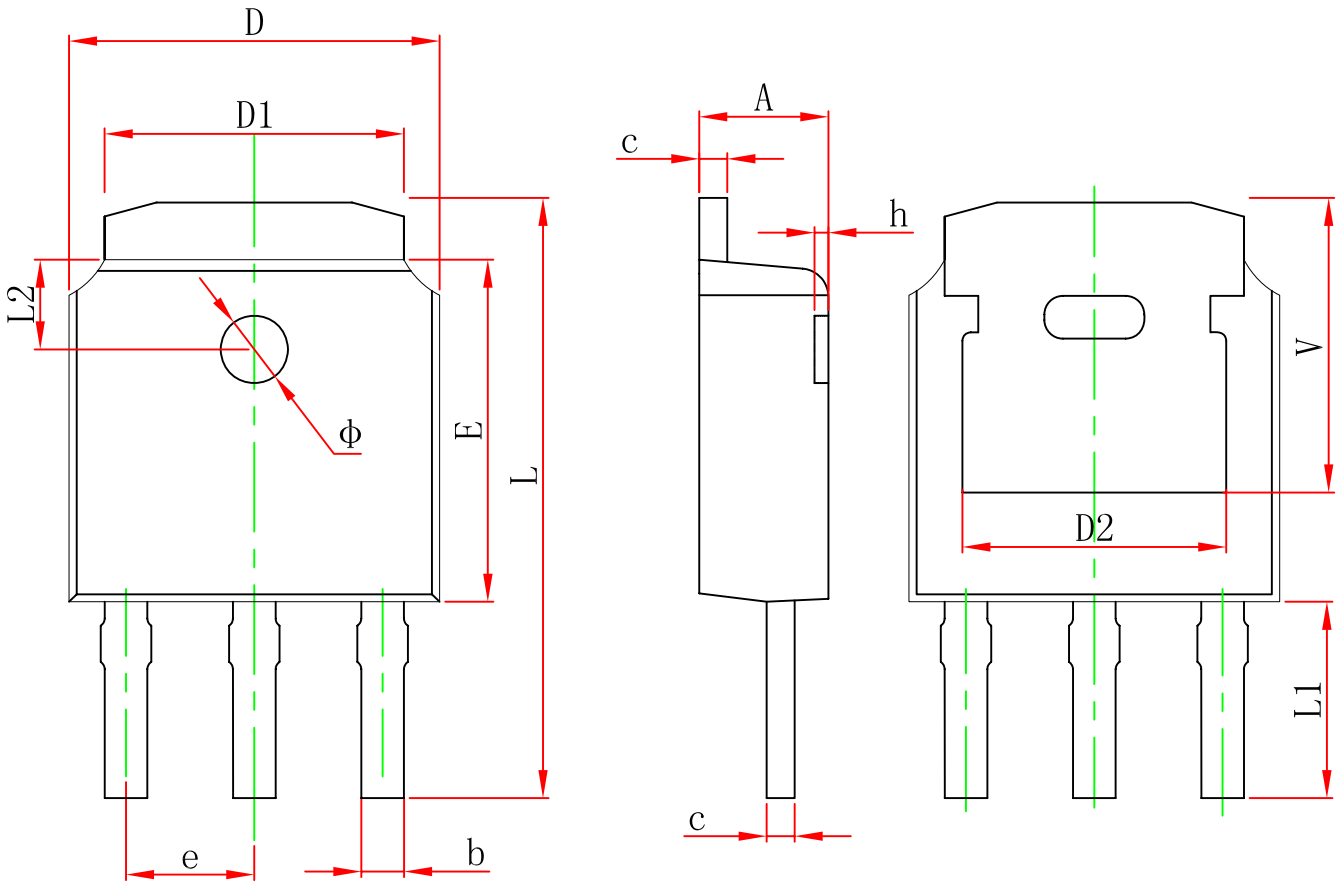
I_S —— V_{SD}



Threshold Voltage



TO-251S Package Outline Dimensions



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	2.200	2.400	0.087	0.094
b	0.660	0.860	0.026	0.034
c	0.460	0.580	0.018	0.023
D	6.500	6.700	0.256	0.264
D1	5.100	5.460	0.201	0.215
D2	4.830 REF.		0.190 REF.	
E	6.000	6.200	0.236	0.244
e	2.186	2.386	0.086	0.094
L	10.312	10.912	0.406	0.430
L1	3.300	3.700	0.130	0.146
L2	1.600 REF.		0.063 REF.	
Φ	1.100	1.300	0.043	0.051
h	0.000	0.300	0.000	0.012
V	5.250 REF.		0.207 REF.	